

JSC "Proton"

Photodiode array chip FM054P

Description

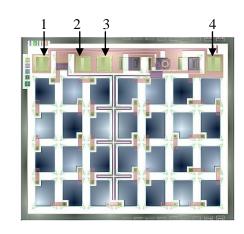
FM054P is designed to drive MOSFETs, including SiC MOSFETs, with threshold voltage 3-7 V and can be used in MOS-relay within one package or as a separate device. The spectral response range is 850 – 940 nm. The chip should be used for face-to-face coupling design together with one IR-LED.

Features

- Contact pad's material Aluminium
- Contact pad's size 0.10 x 0.10 mm
- Module size 1.4 x 1.2 mm (including scribe line)
- Scribe line width 80 μm
- Chip thickness $0.32 \text{ mm} \pm 0.02 \text{ mm}$

Absolute maximum ratings

Storage Temperature	-65°C to 150°C
Operating Junction Temperature	-55°C to 125°C



- 1- Output
- 2 GND
- 3 GND
- 4 Output

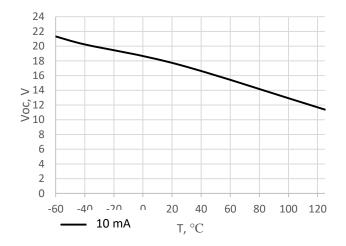
Electrical characteristics (T = 25 °C)

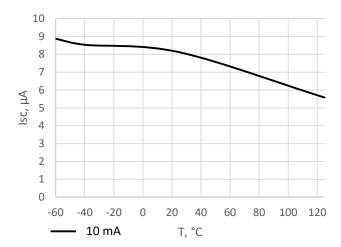
Parameter	Symbol	Unit	Min.	Тур.	Max.	Condition
Open Circuit Voltage	V_{OC}	V	14.0	15.5	-	1
Open Circuit Voltage	V _{OC}	V	-	17	-	2
Short Circuit Current	I_{SC}	μΑ	2.0	2.2	-	1
Short Circuit Current	I_{SC}	μΑ	-	8.1		2
Output Voltage	Vo	V	-	1	0.9	3
Turn-On Time	T _{ON}	ms	-	0.4	1	4
Turn-Off Time	T_{OFF}	ms	-	0.05	0.3	4

- 1 Light source with peak wavelength $\lambda = 850 \pm 20$ nm that provides surface irradiance $E = 20 \text{ mW/cm}^2$ is used.
- 2 Testing condition: I_F = 10 mA. The PDA is assembled with IR-LED of P = 1500 μW (at 10 mA) with peak wavelength λ = 850 ± 20 nm.
- $3 \text{No light. } I_0 = 100 \,\mu\text{A}$
- 4- Typical value at $I_F=10$ mA, $C_L=330$ pF. The PDA is assembled with IR-LED of $P=1500~\mu W$ (at 10 mA) with peak wavelength $\lambda=850\pm20$ nm. The measurement was performed in accordance with the specified testing circuit and diagram.

Typical characteristics

Typical characteristics` measurement is performed on PDA chip assembled with IR-LED chip of P = 1500 μ W (at 10 mA) with peak wavelength λ = 850 \pm 20 nm.





Picture 1 – typical characteristics $V_{OC}(T)$

Picture 2 – typical characteristics I_{SC} (T)

Dynamic parameters testing circuit and diagram

